

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AJT030** is Designed for

FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.5 A
V_{CC}	40 V
P_{DISS}	75 W @ T _C ≤ 85 °C
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	2.2 °C/W

PACKAGE STYLE .400 2L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A		.140 / 3.56
B		.110 / 2.80
C		.110 / 2.80
D	.395 / 10.03	.407 / 10.34
E		.193 / 4.90
F		.230 / 5.84
G	.003 / 0.08	.006 / 0.15
H	.118 / 3.00	.131 / 3.33
I		.063 / 1.60
J		.650 / 16.51
K		.386 / 9.80
L		.900 / 22.86
M		.450 / 11.43
N		.125 / 3.18
O	.050 / 1.27	
P		.405 / 10.29
Q		.170 / 4.32
R		.062 / 1.58

ORDER CODE: ASI10546

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 10 mA	55			V
BV_{CER}	I _C = 20 mA R _{BE} = 10 Ω	55			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CES}	V _{CE} = 35 V			5.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	15		150	---
P_G	V _{CC} = 50 V P _{OUT} = 30 W f = 960 - 1215 MHz	7.8			dB
η_C		40			%